

Simone Balatti

List of Publications by Year in descending order

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2,959
citations

394421

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times ranked

2108
citing authors

#	ARTICLE	IF	CITATIONS
1	Resistive Switching by Voltage-Driven Ion Migration in Bipolar RRAM—Part II: Modeling. IEEE Transactions on Electron Devices, 2012, 59, 2468-2475.	3.0	504
2	Statistical Fluctuations in HfO ₂ Resistive-Switching Memory: Part I - Set/Reset Variability. IEEE Transactions on Electron Devices, 2014, 61, 2912-2919.	3.0	336
3	Resistive Switching by Voltage-Driven Ion Migration in Bipolar RRAM—Part I: Experimental Study. IEEE Transactions on Electron Devices, 2012, 59, 2461-2467.	3.0	215
4	True Random Number Generation by Variability of Resistive Switching in Oxide-Based Devices. IEEE Journal on Emerging and Selected Topics in Circuits and Systems, 2015, 5, 214-221.	3.6	200
5	Neuromorphic Learning and Recognition With One-Transistor-One-Resistor Synapses and Bistable Metal Oxide RRAM. IEEE Transactions on Electron Devices, 2016, 63, 1508-1515.	3.0	192
6	Voltage-Controlled Cycling Endurance of HfO ₂ -Based Resistive-Switching Memory. IEEE Transactions on Electron Devices, 2015, 62, 3365-3372.	3.0	180
7	Analytical Modeling of Oxide-Based Bipolar Resistive Memories and Complementary Resistive Switches. IEEE Transactions on Electron Devices, 2014, 61, 2378-2386.	3.0	171
8	Statistical Fluctuations in HfO ₂ Resistive-Switching Memory: Part II—Random Telegraph Noise. IEEE Transactions on Electron Devices, 2014, 61, 2920-2927.	3.0	161
9	Complementary Switching in Oxide-Based Bipolar Resistive-Switching Random Memory. IEEE Transactions on Electron Devices, 2013, 60, 70-77.	3.0	145
10	Normally-off Logic Based on Resistive Switches—Part I: Logic Gates. IEEE Transactions on Electron Devices, 2015, 62, 1831-1838.	3.0	122
11	Noise-Induced Resistance Broadening in Resistive Switching Memory—Part II: Array Statistics. IEEE Transactions on Electron Devices, 2015, 62, 3812-3819.	3.0	114
12	Evidence for Voltage-Driven Set/Reset Processes in Bipolar Switching RRAM. IEEE Transactions on Electron Devices, 2012, 59, 2049-2056.	3.0	113
13	Impact of the Mechanical Stress on Switching Characteristics of Electrochemical Resistive Memory. Advanced Materials, 2014, 26, 3885-3892.	21.0	97
14	Physical Unbiased Generation of Random Numbers With Coupled Resistive Switching Devices. IEEE Transactions on Electron Devices, 2016, 63, 2029-2035.	3.0	95
15	A 2-transistor/1-resistor artificial synapse capable of communication and stochastic learning in neuromorphic systems. Frontiers in Neuroscience, 2014, 8, 438.	2.8	74
16	Set Variability and Failure Induced by Complementary Switching in Bipolar RRAM. IEEE Electron Device Letters, 2013, 34, 861-863.	3.9	67
17	Noise-Induced Resistance Broadening in Resistive Switching Memory—Part I: Intrinsic Cell Behavior. IEEE Transactions on Electron Devices, 2015, 62, 3805-3811.	3.0	42
18	Postcycling Degradation in Metal-Oxide Bipolar Resistive Switching Memory. IEEE Transactions on Electron Devices, 2016, 63, 4279-4287.	3.0	34

#	ARTICLE	IF	CITATIONS
19	Analytical Modeling of Current Overshoot in Oxide-Based Resistive Switching Memory (RRAM). IEEE Electron Device Letters, 2016, 37, 1268-1271.	3.9	21
20	Size-Dependent Drift of Resistance Due to Surface Defect Relaxation in Conductive-Bridge Memory. IEEE Electron Device Letters, 2012, 33, 1189-1191.	3.9	19
21	Normally-off Logic Based on Resistive Switchesâ€”Part II: Logic Circuits. IEEE Transactions on Electron Devices, 2015, 62, 1839-1847.	3.0	19
22	Data retention statistics and modelling in HfO ₂ /resistive switching memories. , 2015, , .		11
23	Investigation of Gate-Length Scaling of Ferroelectric FET. IEEE Transactions on Electron Devices, 2021, 68, 1364-1368.	3.0	9
24	Filament Evolution during Set and Reset Transitions in Oxide Resistive Switching Memory. Japanese Journal of Applied Physics, 2013, 52, 04CD10.	1.5	8
25	Physical modeling of voltage-driven resistive switching in oxide RRAM. , 2012, , .		6
26	Scaling behavior of ferroelectric FET with reduction in number of domains in ferroelectric layer. Japanese Journal of Applied Physics, 2022, 61, SC1030.	1.5	4